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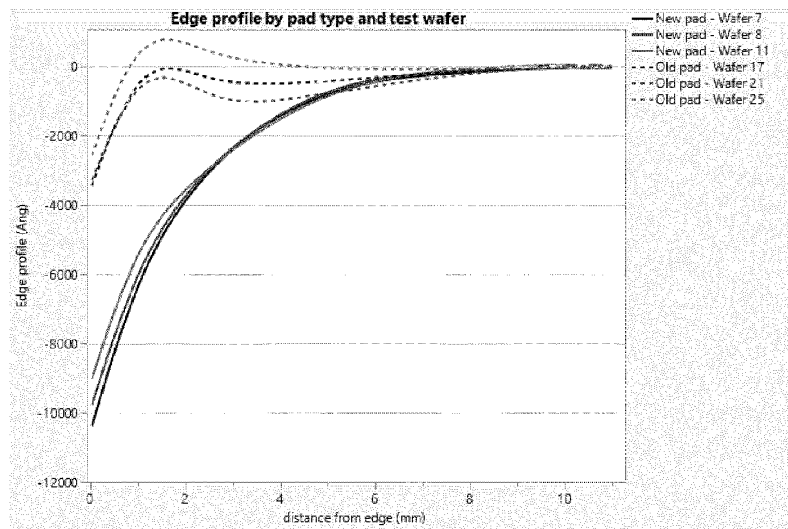
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(54) Title: MANUFACTURING OF A DONOR SUBSTRATE FOR THE MANUFACTURE OF A POI STRUCTURE

[Fig. 2]



(57) Abstract: The present invention relates to a method of manufacturing a donor substrate for the manufacture of a Piezoelectric on Insulator, POI, structure, comprising providing a support substrate, forming a block of piezoelectric material on or over the support substrate, wherein the piezoelectric material comprises or consists of one of lithium tantalate and lithium niobate, chemical-mechanical polishing, CMP, the block of piezoelectric material to obtain a piezoelectric substrate and implanting a species into the piezoelectric substrate to obtain a weakened layer in the piezoelectric substrate. The CMP is performed by means of a CMP pad comprising a sub pad with a hardness of more than 45 shore A.

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